EAST - [thinhsearch15.wsp:1]

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- L3: (8) "6277706"
- L1: (87) "5447884"
- L4: (100) 1 2 3
- L5: (223) silicon adj nitride adj liner
- L7: (9461) STI
- L8: (9720) Shallow adj trench adj isolation
- L9: (12906) 7 8
- L10: (88) 5 and 7
- L11: (120) 5 and 8
- L12: (288214) heal$4
- L13: (5) 10 and 12
- L14: (5) 11 and 12
- L15: (86) silicon adj oxide adj liner
- L16: (15840) current adj drive
- L17: (30768) cache adj memory
- L19: (180) tag adj cells
- L20: (0) 19 and 18
- L18: (104) 16 and 17
- L6: (19) 5 and 4
- L2: (8) "6051478"

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DBs USPAT;US-PGPUB;EPO;JPO;DERWENT;IBM_TDB

Default operator: OR

Plurals | Highlight all hit terms initially

11 and 12

| | U | 1 | Document ID | Issue Date | Pages | Title | Current OR | Current XRef | Retrieval Cla | Inventor | S | C | P | 2 | 3 | Image Do |
|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|
| 1 | ☐ | ☐ | US 20030109140 A1 | 20030612 | 13 | Buried strap formation method for sub-150 nm best DRAM devices | 438/694 | 257/E21.653; 438/689 | | Lee, Brian | ☑ | ☐ | ☐ | ☐ | ☐ | US 200301 |
| 2 | ☑ | ☐ | US 20030045070 A1 | 20030306 | 9 | Method and device for forming an STI type isolation in a semiconductor | 438/424 | 257/E21.546 | | Kim, Chul-Sung et al. | ☐ | ☐ | ☐ | ☐ | ☐ | US 200300 |
| 3 | ☑ | ☐ | US 6660613 B2 | 20031209 | 8 | Method and device for forming an STI type isolation in a semiconductor | 438/424 | 257/E21.546; 438/435; | | Kim, Chul-Sung et al. | ☐ | ☐ | ☐ | ☐ | ☐ | US 666061 |
| 4 | ☐ | ☐ | US 6528367 B1 | 20030304 | 16 | Self-aligned active array along the length direction to form un-biased bur | 438/253 | 257/298; 438/238; | | Lee, Brian | ☑ | ☐ | ☐ | ☐ | ☐ | US 652836 |
| 5 | ☐ | ☐ | US 6140208 A | 20001031 | 10 | Shallow trench isolation (STI) with bilayer of oxide-nitride for VLSI appli | 438/437 | 257/E21.546; 438/435 | | Agahi, Farid et al. | ☑ | ☐ | ☐ | ☐ | ☐ | US 614020 |

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